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CY7C109BN
CY7C1009BN

128K x 8 Static RAM

Features

- **High speed**
  - **— t_{AA} = 12 ns**
- **Low active power**
  - **— 495 mW (max. 12 ns)**
- **Low CMOS standby power**
  - **— 55 mW (max.) 4 mW**
- **2.0V Data Retention**
- **Automatic power-down when deselected**
- **TTL-compatible inputs and outputs**
- **Easy memory expansion with $\overline{CE}_1$, CE_2, and $\overline{OE}$ options**

Functional Description[1]

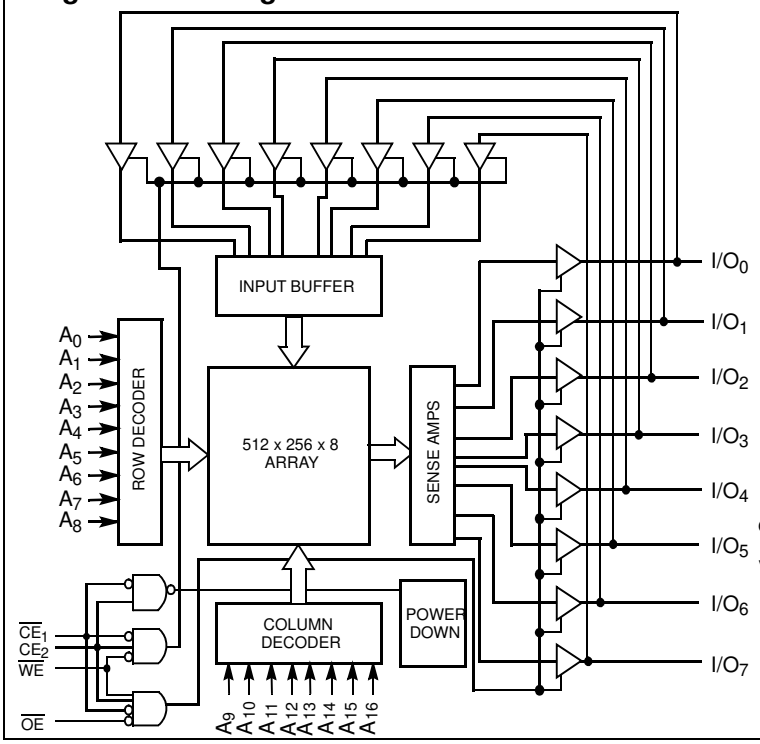
The CY7C109BN/CY7C1009BN is a high-performance CMOS static RAM organized as 131,072 words by 8 bits. Easy memory expansion is provided by an active LOW Chip Enable ($\overline{CE}_1$), an active HIGH Chip Enable (CE_2), an active LOW Output Enable ($\overline{OE}$), and three-state drivers. Writing to the device is accomplished by taking Chip Enable One ($\overline{CE}_1$) and Write Enable ($\overline{WE}$) inputs LOW and Chip Enable Two (CE_2) input HIGH. Data on the eight I/O pins (I/O_0 through I/O_7) is then written into the location specified on the address pins (A_0 through A_{16}).

Reading from the device is accomplished by taking Chip Enable One ($\overline{CE}_1$) and Output Enable ($\overline{OE}$) LOW while forcing Write Enable ($\overline{WE}$) and Chip Enable Two (CE_2) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

The eight input/output pins (I/O_0 through I/O_7) are placed in a high-impedance state when the device is deselected ($\overline{CE}_1$ HIGH or CE_2 LOW), the outputs are disabled ($\overline{OE}$ HIGH), or during a write operation ($\overline{CE}_1$ LOW, CE_2 HIGH, and $\overline{WE}$ LOW).

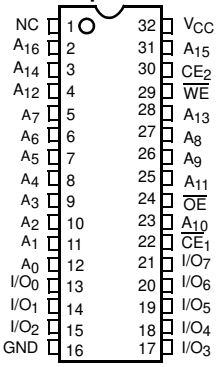
The CY7C109BN is available in standard 400-mil-wide SOJ and 32-pin TSOP type I packages. The CY7C1009BN is available in a 300-mil-wide SOJ package. The CY7C1009BN and CY7C109BN are functionally equivalent in all other respects.

Logic Block Diagram

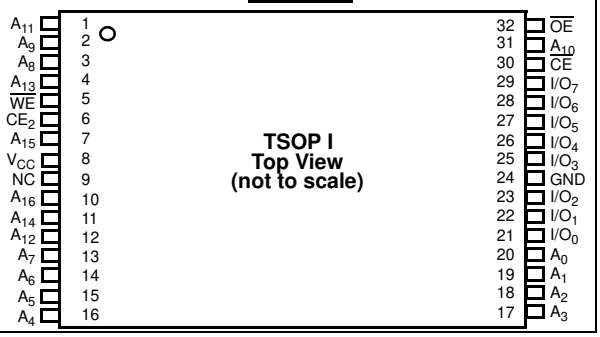


Pin Configurations

SOJ
Top View



TSOP I
Top View
(not to scale)



Note:
1. For guidelines on SRAM system design, please refer to the 'System Design Guidelines' Cypress application note, available on the internet at www.cypress.com.

Selection Guide

		7C109B-12 7C1009B-12	7C109B-15 7C1009B-15	7C109B-20 7C1009B-20	Unit
Maximum Access Time		12	15	20	ns
Maximum Operating Current		90	80	75	mA
Maximum CMOS Standby Current		10	10	10	mA
	L	2	2	2	mA

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....–65°C to +150°C

Ambient Temperature with Power Applied.....–55°C to +125°C

Supply Voltage on V_{CC} to Relative GND[2] .... –0.5V to +7.0V

DC Voltage Applied to Outputs in High Z State[2] .....–0.5V to V_{CC} + 0.5V

DC Input Voltage[2].....–0.5V to V_{CC} + 0.5V

Current into Outputs (LOW)..... 20 mA

Static Discharge Voltage.....>2001V (per MIL-STD-883, Method 3015)

Latch-Up Current .....>200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Commercial	0°C to +70°C	5V ± 10%
Industrial	–40°C to +85°C	5V ± 10%

Electrical Characteristics Over the Operating Range

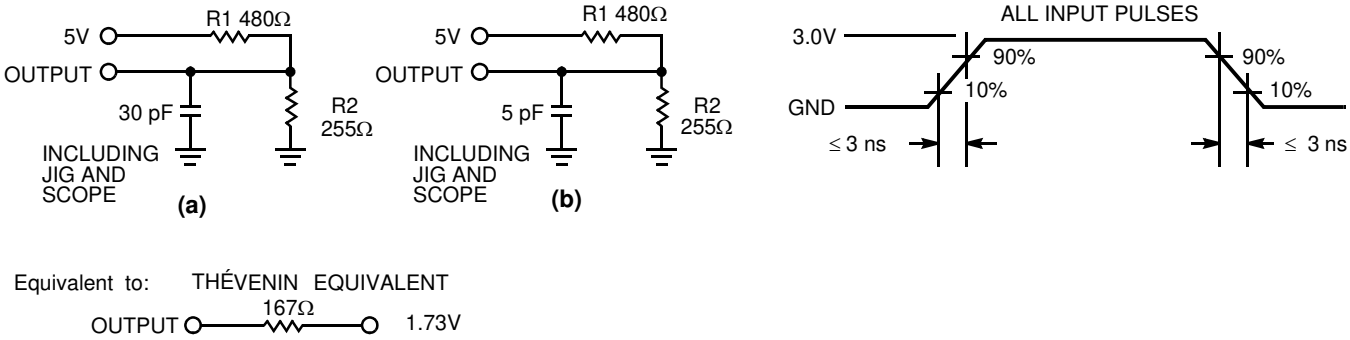
Parameter	Description	Test Conditions		7C109BN-12 7C1009BN-12		7C109BN-15 7C1009BN-15		7C109BN-20 7C1009BN-20		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = –4.0 mA		2.4		2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA			0.4		0.4		0.4	V
V_{IH}	Input HIGH Voltage			2.2	V_{CC} + 0.3	2.2	V_{CC} + 0.3	2.2	V_{CC} + 0.3	V
V_{IL}	Input LOW Voltage[2]			–0.3	0.8	–0.3	0.8	–0.3	0.8	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1	+1	–1	+1	–1	+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_I ≤ V_{CC}, Output Disabled		–5	+5	–5	+5	–5	+5	µA
I_{OS}	Output Short Circuit Current[3]	V_{CC} = Max., V_{OUT} = GND			–300		–300		–300	mA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., I_{OUT} = 0 mA, f = f_{MAX} = $1/t_{RC}$			90		80		75	mA
I_{SB1}	Automatic CE Power-Down Current —TTL Inputs	Max. V_{CC}, $\overline{CE_1}$ ≥ V_{IH} or CE_2 ≤ V_{IL}, V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}			45		40		30	mA
I_{SB2}	Automatic CE Power-Down Current —CMOS Inputs	Max. V_{CC}, $\overline{CE_1}$ ≥ V_{CC} – 0.3V, or CE_2 ≤ 0.3V, V_{IN} ≥ V_{CC} – 0.3V, or V_{IN} ≤ 0.3V, f = 0			10		10		10	mA
			L		2		2		2	mA

Capacitance[4]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 5.0V	9	pF
C_{OUT}	Output Capacitance		8	pF

Notes:
2. Minimum voltage is –2.0V for pulse durations of less than 20 ns.
3. Not more than one output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
4. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms



Equivalent to: THÉVENIN EQUIVALENT

Switching Characteristics[5] Over the Operating Range

Parameter	Description	7C109BN-12 7C1009BN-12		7C109BN-15 7C1009BN-15		7C109BN-20 7C1009BN-20		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle								
t_{RC}	Read Cycle Time	12		15		20		ns
t_{AA}	Address to Data Valid		12		15		20	ns
t_{OHA}	Data Hold from Address Change	3		3		3		ns
t_{ACE}	$\overline{CE}_1$ LOW to Data Valid, CE_2 HIGH to Data Valid		12		15		20	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		6		7		8	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z	0		0		0		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[6, 7]		6		7		8	ns
t_{LZCE}	$\overline{CE}_1$ LOW to Low Z, CE_2 HIGH to Low Z[7]	3		3		3		ns
t_{HZCE}	$\overline{CE}_1$ HIGH to High Z, CE_2 LOW to High Z[6, 7]		6		7		8	ns
t_{PU}	$\overline{CE}_1$ LOW to Power-Up, CE_2 HIGH to Power-Up	0		0		0		ns
t_{PD}	$\overline{CE}_1$ HIGH to Power-Down, CE_2 LOW to Power-Down		12		15		20	ns
Write Cycle[8]								
t_{WC}	Write Cycle Time[9]	12		15		20		ns
t_{SCE}	$\overline{CE}_1$ LOW to Write End, CE_2 HIGH to Write End	10		12		15		ns
t_{AW}	Address Set-Up to Write End	10		12		15		ns
t_{HA}	Address Hold from Write End	0		0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	10		12		12		ns
t_{SD}	Data Set-Up to Write End	7		8		10		ns
t_{HD}	Data Hold from Write End	0		0		0		ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[7]	3		3		3		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[6, 7]		6		7		8	ns

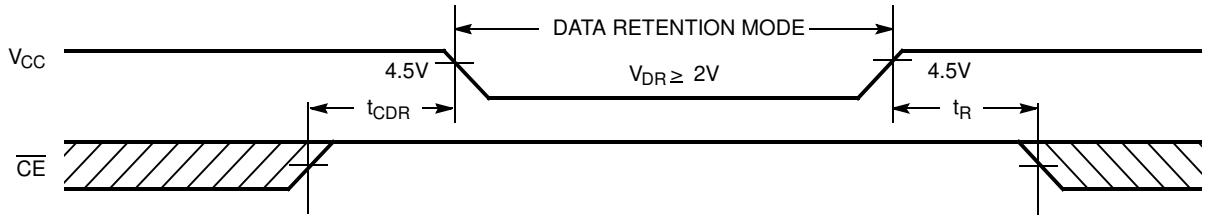
Notes:

5. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
6. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
7. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
8. The internal write time of the memory is defined by the overlap of $\overline{CE}_1$ LOW, CE_2 HIGH, and $\overline{WE}$ LOW. $\overline{CE}_1$ and $\overline{WE}$ must be LOW and CE_2 HIGH to initiate a write, and the transition of any of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
9. The minimum write cycle time for Write Cycle No. 3 ($\overline{WE}$ controlled, $\overline{OE}$ LOW) is the sum of t_{HZWE} and t_{SD}.

Data Retention Characteristics Over the Operating Range **(Low Power version only)**

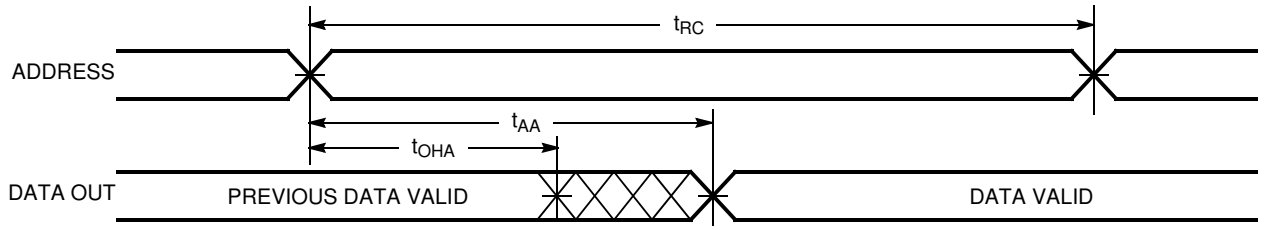
Parameter	Description	Conditions	Min.	Max	Unit
V_{DR}	V_{CC} for Data Retention	No input may exceed V_{CC} + 0.5V $\overline{V_{CC}}$ = V_{DR} = 2.0V, $\overline{CE_1} \geq V_{CC} - 0.3V$ or $CE_2 \leq 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$	2.0		V
I_{CCDR}	Data Retention Current			150	µA
t_{CDR}	Chip Deselect to Data Retention Time		0		ns
t_R	Operation Recovery Time		200		µs

Data Retention Waveform

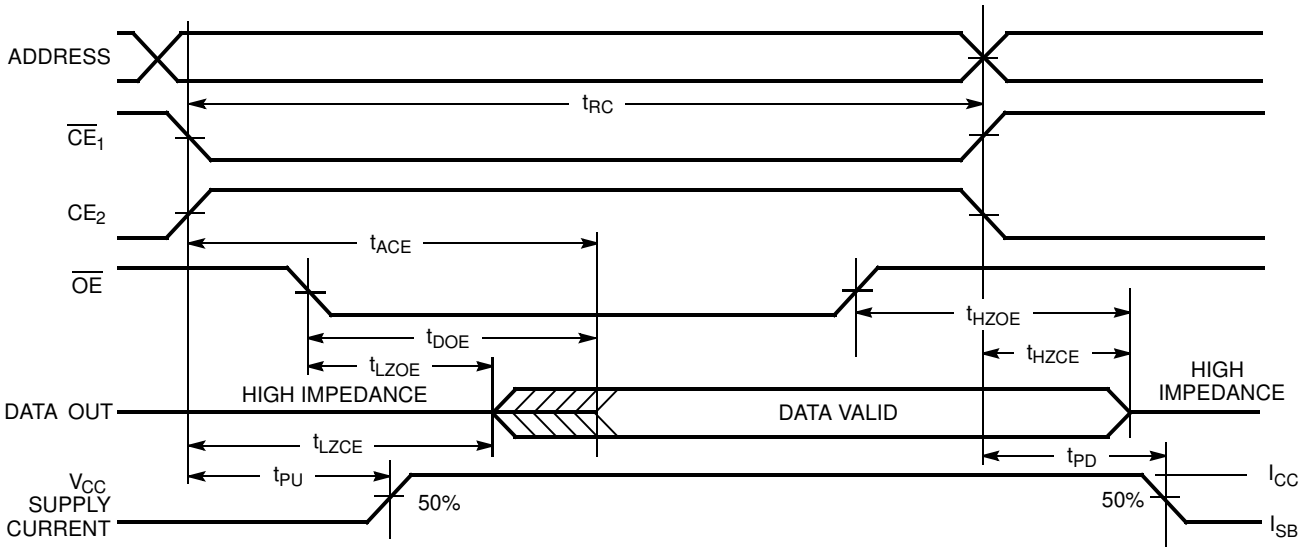


Switching Waveforms

Read Cycle No. 1[10, 11]



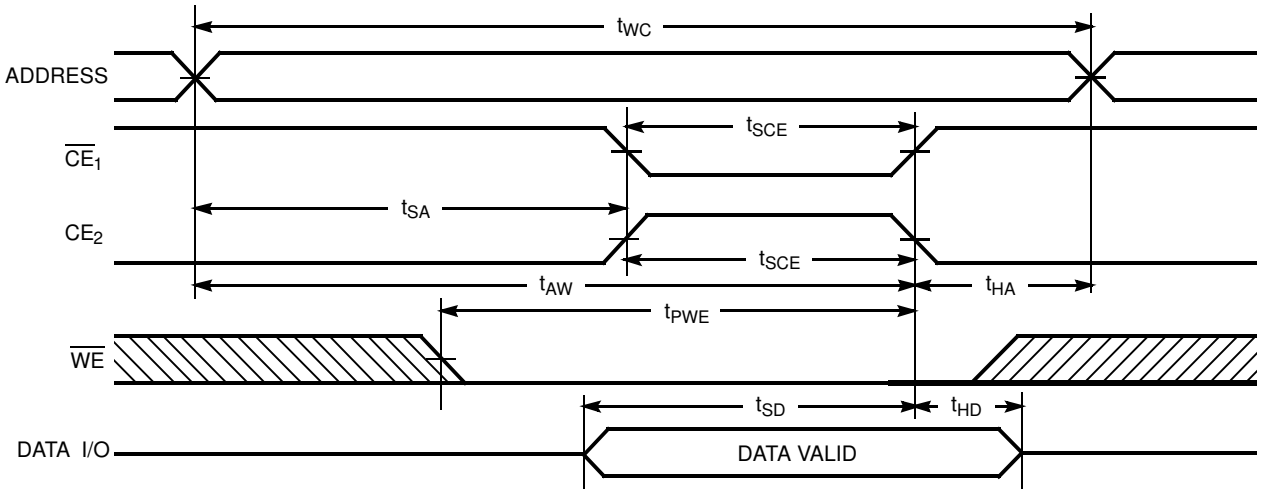
Read Cycle No. 2 ($\overline{OE}$ Controlled)[11, 12]



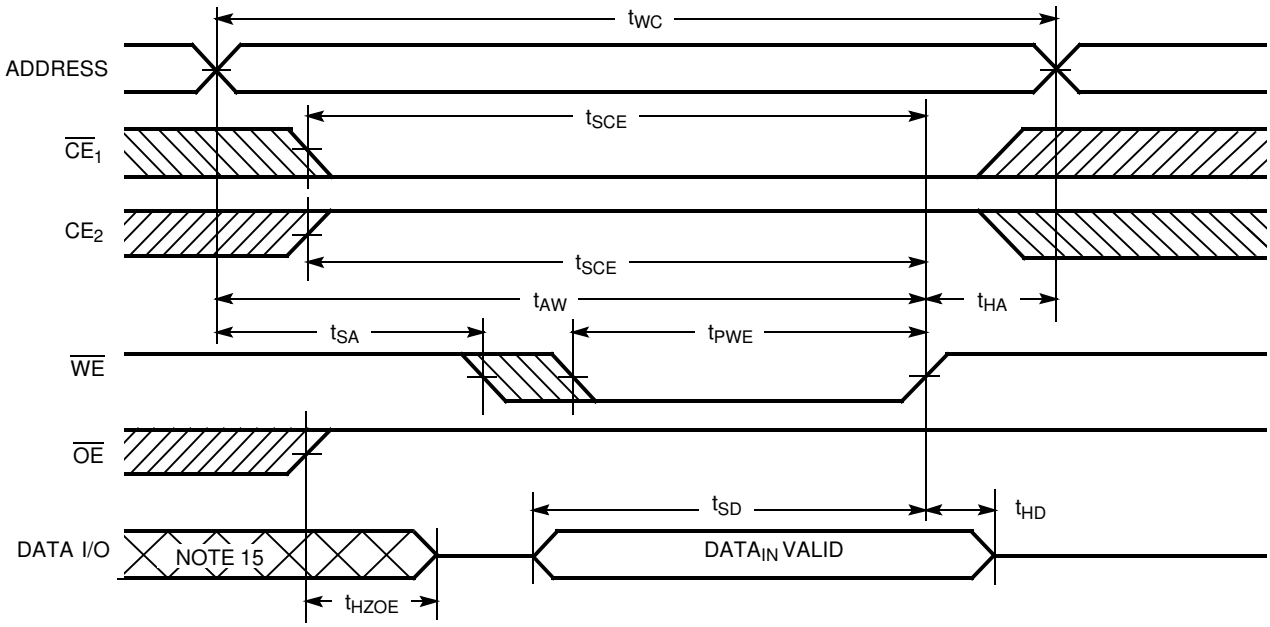
Notes:
10. Device is continuously selected. $\overline{OE}$, $\overline{CE_1}$ = V_{IL}, CE_2 = V_{IH}.
11. $\overline{WE}$ is HIGH for read cycle.
12. Address valid prior to or coincident with $\overline{CE_1}$ transition LOW and CE_2 transition HIGH.

Switching Waveforms (continued)

Write Cycle No. 1 ($\overline{CE}_1$ or CE_2 Controlled)[13, 14]



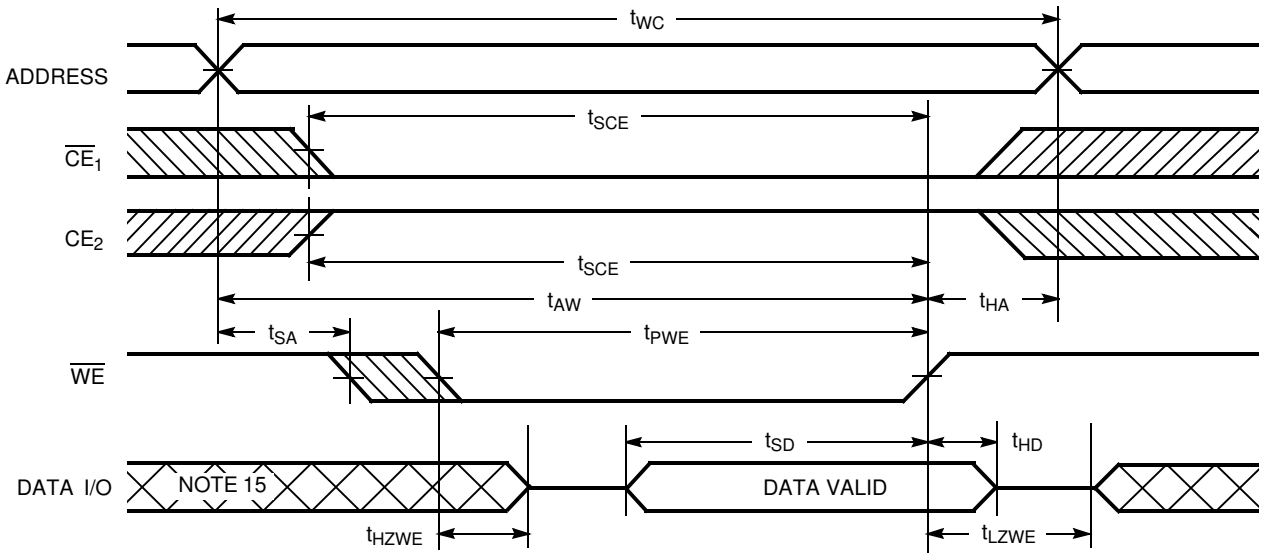
Write Cycle No. 2 ($\overline{WE}$ Controlled, $\overline{OE}$ HIGH During Write)[13, 14]



Notes:
13. Data I/O is high impedance if $\overline{OE}$ = V_{IH}.
14. If $\overline{CE}_1$ goes HIGH or CE_2 goes LOW simultaneously with $\overline{WE}$ going HIGH, the output remains in a high-impedance state.
15. During this period the I/Os are in the output state and input signals should not be applied.

Switching Waveforms (continued)

Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)[14]



Truth Table

$\overline{CE_1}$	CE_2	$\overline{OE}$	$\overline{WE}$	I/O_0–I/O_7	Mode	Power
H	X	X	X	High Z	Power-Down	Standby (I_{SB})
X	L	X	X	High Z	Power-Down	Standby (I_{SB})
L	H	L	H	Data Out	Read	Active (I_{CC})
L	H	X	L	Data In	Write	Active (I_{CC})
L	H	H	H	High Z	Selected, Outputs Disabled	Active (I_{CC})

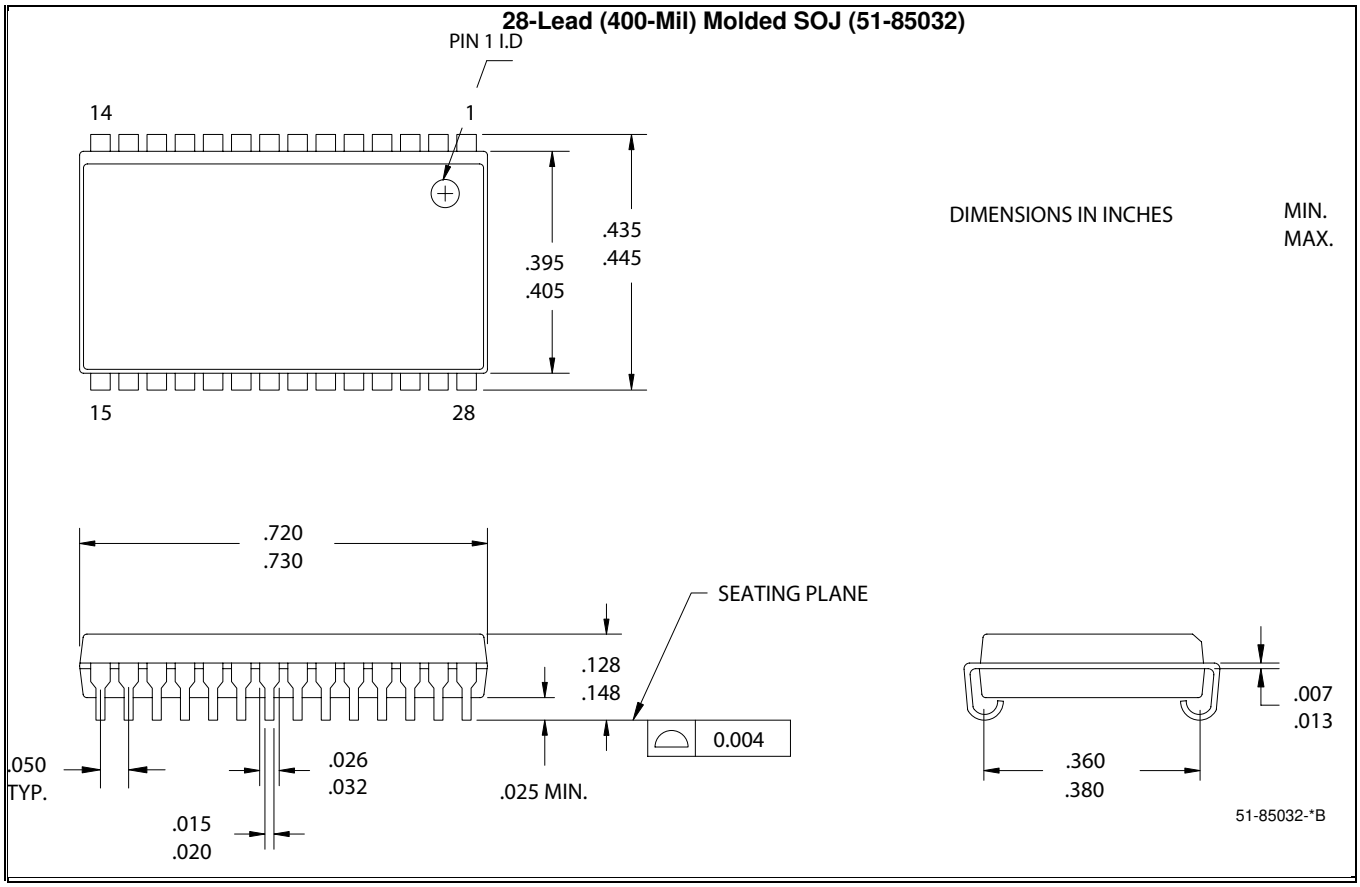
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
12	CY7C109BN-12VC	51-85032	32-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1009BN-12VC	51-85031	32-Lead (300-Mil) Molded SOJ	
	CY7C109BN-12ZC	51-85056	32-Lead TSOP Type I	
	CY7C109BN-12ZXC	51-85056	32-Lead TSOP Type I (Pb-free)	
15	CY7C109BNL-15VC	51-85032	32-Lead (400-Mil) Molded SOJ	Commercial
	CY7C109BN-15VC	51-85032	32-Lead (400-Mil) Molded SOJ	
	CY7C1009BN-15VC	51-85031	32-Lead (300-Mil) Molded SOJ	
	CY7C109BN-15ZC	51-85056	32-Lead TSOP Type I	
	CY7C109BN-15ZXC	51-85056	32-Lead TSOP Type I (Pb-free)	
	CY7C109BN-15VI	51-85032	32-Lead (400-Mil) Molded SOJ	Industrial
	CY7C1009BN-15VI	51-85031	32-Lead (300-Mil) Molded SOJ	
20	CY7C109BN-20VC	51-85032	32-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1009BN-20VC	51-85031	32-Lead (300-Mil) Molded SOJ	
	CY7C109BN-20VI	51-85032	32-Lead (400-Mil) Molded SOJ	Industrial
	CY7C109BN-20ZC	51-85056	32-Lead TSOP Type I	Commercial
	CY7C109BN-20ZXC	51-85056	32-Lead TSOP Type I (Pb-free)	

Please contact local sales representative regarding availability of these parts

Package Diagrams

28-Lead (400-Mil) Molded SOJ (51-85032)

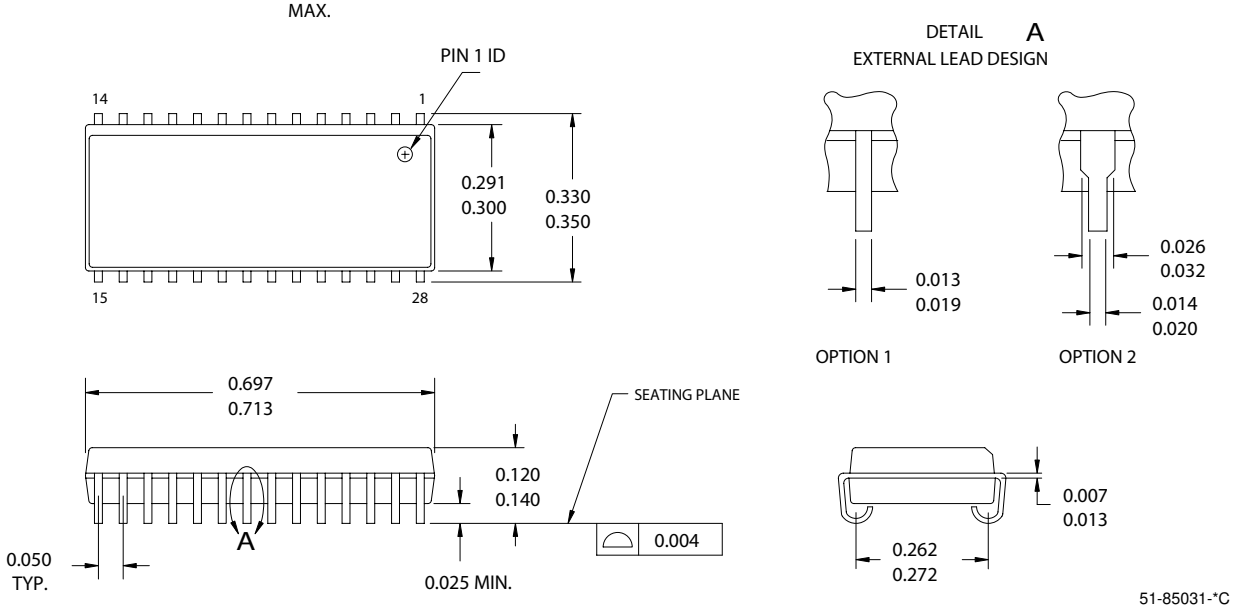


Package Diagrams (continued)

28-Lead (300-Mil) Molded SOJ (51-85031)

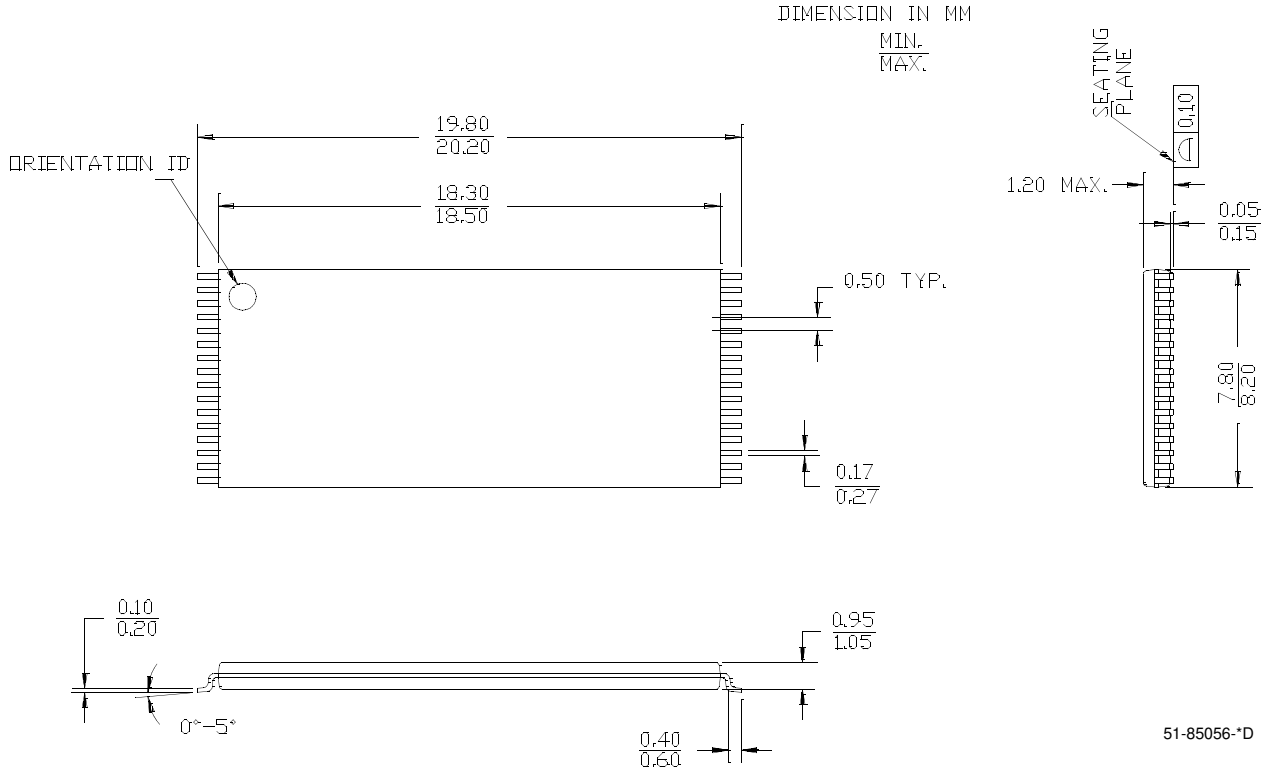
NOTE :

1. JEDEC STD REF MO088
2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH
   MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.006 in (0.152 mm) PER SIDE
3. DIMENSIONS IN INCHES MIN.
   MAX.



51-85031-*C

32-Lead TSOP I (8x20 mm) (51-85056)



51-85056-*D

Document History Page

Document Title: CY7C109BN/CY7C1009BN 128K x 8 Static RAM Document Number: 001-06430				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	423847	See ECN	NXR	New Data Sheet